

2SB1132

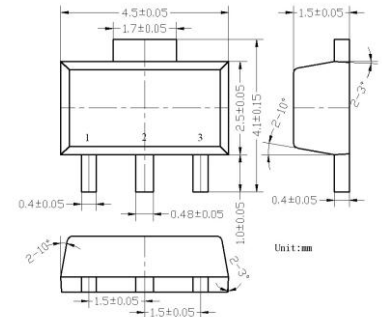
2SB1132 TRANSISTOR (PNP)

Features:

Compliments 2SD1664

MAXIMUM RATINGS ($T_a=25^\circ\text{C}$ unless otherwise noted)

| Symbol | Parameter | Value | Unit |
|-----------|------------------------------|---------|------------------|
| V_{CB0} | Collector-Base Voltage | -40 | V |
| V_{CEO} | Collector-Emitter Voltage | -32 | V |
| V_{EBO} | Emitter-Base Voltage | -5 | V |
| I_C | Collector Current-Continuous | -1 | A |
| I_{CP} | Collector Current -Pulsed | -2 | A |
| P_C | Collector Power Dissipation | 500 | mW |
| T_j | Junction Temperature | 150 | $^\circ\text{C}$ |
| T_{stg} | Storage Temperature | -55-150 | $^\circ\text{C}$ |



1. BASE
2. COLLECTOR
3. EMITTER

ELECTRICAL CHARACTERISTICS ($T_a=25^\circ\text{C}$ unless otherwise specified)

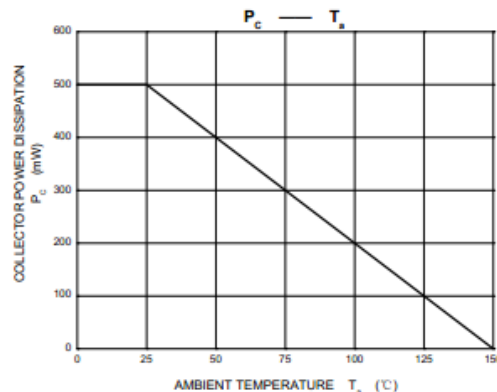
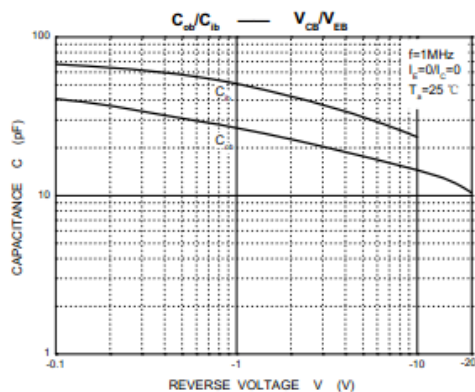
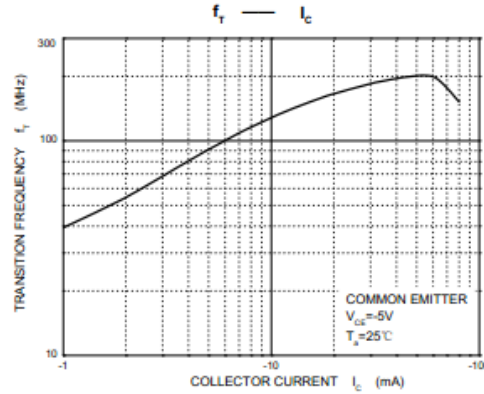
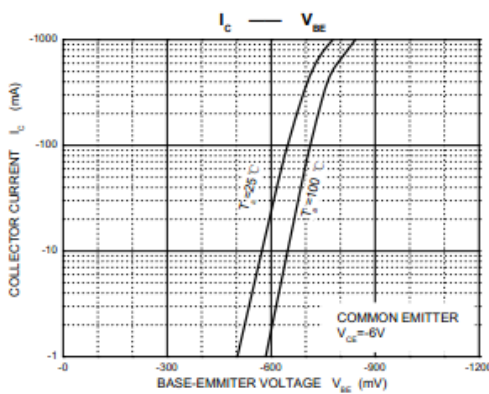
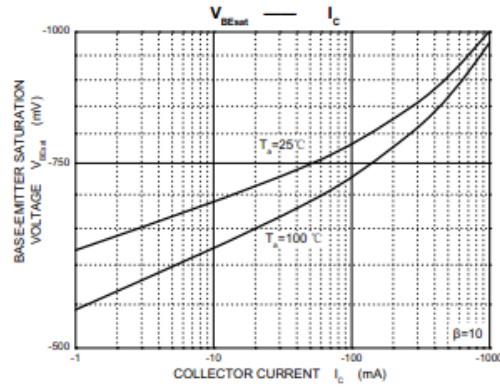
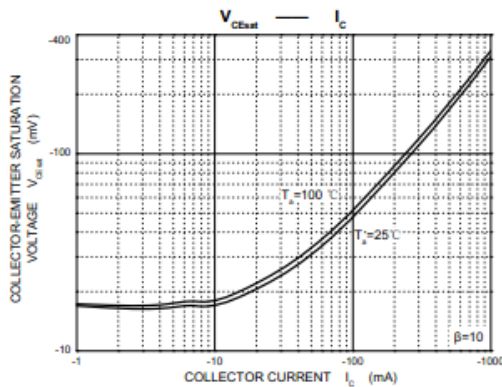
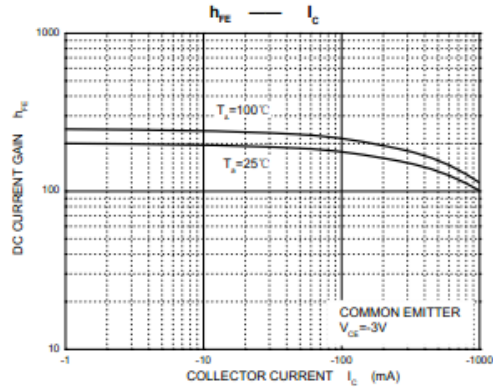
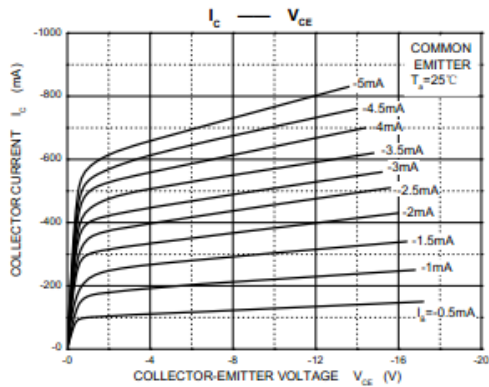
| Parameter | Symbol | Test conditions | Min | Typ | Max | Unit |
|---------------------------------------|---------------|---|-----|------|------|---------------|
| Collector-base breakdown voltage | $V_{(BR)CB0}$ | $I_C = -50\mu\text{A}, I_E = 0$ | -40 | | | V |
| Collector-emitter breakdown voltage * | $V_{(BR)CEO}$ | $I_C = -1\text{mA}, I_B = 0$ | -32 | | | V |
| Emitter-base breakdown voltage | $V_{(BR)EBO}$ | $I_E = -50\mu\text{A}, I_C = 0$ | -5 | | | V |
| Collector cut-off current | I_{CB0} | $V_{CB} = -20\text{V}, I_E = 0$ | | | -0.5 | μA |
| Emitter cut-off current | I_{EBO} | $V_{EB} = -4\text{V}, I_C = 0$ | | | -0.5 | μA |
| DC current gain | $h_{FE(1)}$ | $V_{CE} = -3\text{V}, I_C = -100\text{mA}$ | 82 | | 390 | |
| Collector-emitter saturation voltage | $V_{CE(sat)}$ | $I_C = -500\text{mA}, I_B = -50\text{mA}$ | | -0.2 | -0.5 | V |
| Transition frequency | f_T | $V_{CE} = -5\text{V}, I_C = -50\text{mA}, f = 30\text{MHZ}$ | | 150 | | MHZ |
| Collector output capacitance | C_{ob} | $V_{CB} = -10\text{V}, I_E = 0, f = 1\text{MHZ}$ | | 20 | 30 | PF |

CLASSIFICATION OF h_{FE}

| Rank | P | Q | R |
|---------|--------|---------|---------|
| Range | 82-180 | 120-270 | 180-390 |
| Marking | BAP | BAQ | BAR |

Typical Characteristics

2SB1132



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